

PHOTOTRANSISTOR

Part Number: L-53P3C

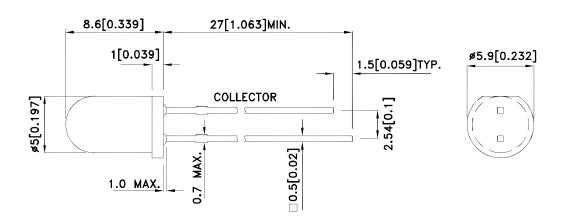
Features

- Mechanically and spectrally matched to the infrared emitting LED lamp .
- RoHS compliant.

Description

Made with NPN silicon phototansistor chips.

Package Dimensions



- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
- 3. Lead spacing is measured where the leads emerge from the package.
 4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

SPEC NO: DSAA4158 APPROVED: WYNEC

REV NO: V.12 CHECKED: Allen Liu

DATE: MAR/09/2012 DRAWN: D.M.Su





Kingbright

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30			V	Ic=100uA Ee=0mW/c m³
VBR ECO	Emitter-to-Collector Breakdown Voltage	5			V	IE=100uA Ee=0mW/c m²
VCE (SAT)	Collector-to-Emitter Saturation Voltage			0.8	V	Ic=2mA Ee=20mW/c m³
I CEO	Collector Dark Current			100	nA	Vc=10V Ee=0mW/c m³
TR	Rise Time (10% to 90%)		15		us	VCE = 5V IC=1mA RL=1000Ω
TF	Fall Time (90% to 10%)		15		us	
I (ON)	On State Collector Current	0.7	3		mA	VcE = 5V Ee=1mW/c m [*] λ=940nm

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings			
Collector-to-Emitter Voltage	30V			
Emitter-to-Collector Voltage	5V			
Power Dissipation at (or below) 25°C Free Air Temperature	100mW			
Operating Temperature	-40°C To +85°C			
Storage Temperature	-40°C To +85°C			
Lead Soldering Temperature (>5mm for 5sec)	260°C			

REV NO: V.12 DATE: MAR/09/2012 SPEC NO: DSAA4158 PAGE: 2 OF 5 DRAWN: D.M.Su

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